

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

1-3. (cancelled)

4. (original) A method of manufacturing an in-plane switching liquid crystal display having thin film transistors on a substrate, scan lines and signal lines connected to the thin film transistors and longitudinally and latitudinally crossing each other, and common wiring formed by the same layer as the scan lines and generating electric fields substantially parallel to the substrate between a common electrode connected to the common wiring and covering the signal lines partially via an interlayer insulating film formed on the thin film transistors, and pixel electrodes connected to the thin film transistors, the method comprising the steps of:

forming a first inorganic insulating film on the thin film transistors,

forming first contact holes for connecting the common wiring and the common electrode to each other, and second contact holes for connecting the thin film transistors and the pixel electrodes to each other using at least dry etching,

forming a second inorganic insulating film on the first inorganic insulating film,

forming third contact holes so as to be superposed on the first contact holes, and fourth contact holes so as to be superposed on the second contact holes,

forming a conductive film on the second inorganic insulating film,

forming the common electrode connected to the common wiring via the first and third contact holes, and

forming the pixel electrodes connected to the thin film transistors via the second and fourth contact holes.

5. (original) A method according to claim 4, wherein:

the third contact holes are formed inside the first contact holes while the fourth contact holes are formed inside said second contact holes.

6. (original) A method of manufacturing an in-plane switching liquid crystal display having thin film transistors on a substrate, scan lines and signal lines connected to the thin film transistors and longitudinally and latitudinally crossing each other, and common wiring formed by the same layer as the scan lines and generating electric fields substantially parallel to the substrate between a common electrode connected to the common wiring and covering the signal lines partially via an interlayer insulating film formed on the thin film transistors, and pixel electrodes connected to the thin film transistors, wherein:

the interlayer insulating film is formed by an

inorganic insulating film, and

a thickness of the inorganic insulating film is set to be greater than at least a thickness of a portion of the insulating film where contact holes for connecting the common wiring and the common electrode to each other are formed by dry etching.